

ABSTRACT OF THE DISCLOSURE

5 An etching method is carried out by an etching system comprising a gas supply port for supplying an etching gas, a plasma producing vessel defining a plasma producing chamber in which the etching gas is converted into a plasma to produce radicals, a reaction vessel connected to the plasma producing vessel and defining a reaction chamber of a diameter greater than that of the plasma producing chamber, a support table placed in the reaction chamber to support an object to be processed to be etched by the radicals flowing
10 down thereto from the plasma producing chamber, and a vacuum exhaust system for evacuating the reaction chamber. The etching gas is supplied through the etching gas supply port at an etching gas supply rate of 8.4 sccm or above per a substantial volume of one liter of the reaction chamber.